

## NPN T-1 Standard Phototransistor

LTR-4206/LTR-4206E

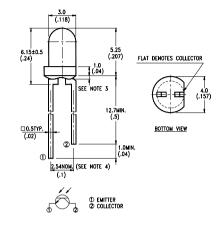
### Features

- · Wide range of collector currents.
- · Lens for high sensitivity.
- · Low cost plastic package.

## Description

The LTR-4206 series consist of a NPN silicon phototransistor mounted in a lensed, clear plastic, end looking package. The lensing effect of the package allows an acceptance half angle of 10° measured from the optical axis to the half power point. This series is mechanically and spectrally matched to the LTE-4206 series of infrared emitting diodes. The LTR-4206E is a special dark plastic package that cut the visible light and suitable for the detectors of infrared application.

## **Package Dimensions**



#### Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is  $\pm$  0.25mm (.010") unless otherwise noted.
- 3. Protruded resin under flange is 1.5mm (.059") max.
- 4. Lead spacing is measured where the leads emerge from the package.
- 5. Specifications are subject to change without notice.

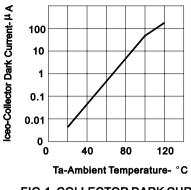
## Absolute Maximum Ratings at Ta=25°C

| Parameter  | Maximum Rating      | Unit |  |  |  |
|--|---------------------|------|--|--|--|
| Power Dissipation  | 100                 | mW   |  |  |  |
| Collector-Emitter Voltage                                  | 30                  | V    |  |  |  |
| Emitter-Collector Voltage                                  | 5                   | V    |  |  |  |
| Operating Temperature Range                                | -40°C to +85°C      |      |  |  |  |
| Storage Temperature Range                                  | -55°C to +100°C     |      |  |  |  |
| Lead Soldering Temperature<br>[1.6mm (.063 in.) from body] | 260°C for 5 Seconds |      |  |  |  |

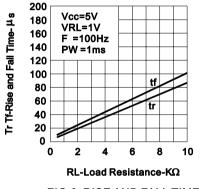
## Electrical Optical Characteristics at Ta=25°C

| Parameter                            | Symbol   | Part No.  | Min. | Тур. | Max. | Unit | Test<br>Condition                    |
|--------------------------------------|----------|-----------|------|------|------|------|--------------------------------------|
| Collector-Emitter Breakdown Voltage  | V(BR)CEO |           | 30   |      |      | V    | Ic=1mA<br>Ee=0mW/cm <sup>2</sup>     |
| Emitter-Collector Breakdown Voltage  | V(BR)ECO |           | 5    |      |      | V    | IE=100 μ A<br>Ee=0mW/cm <sup>2</sup> |
| Collector Emitter Saturation Voltage | VCE(SAT) |           |      |      | 0.4  | V    | Ic=100 μ A<br>Ee=1mW/cm <sup>2</sup> |
| Rise Time                            | Tr       |           |      | 10   |      | μS   | Vcc=5V<br>Ic=1mA                     |
| Fall Time                            | Tf       |           |      | 15   |      | μS   | R∟=1K Ω                              |
| Collector Dark Current               | ICEO     |           |      |      | 100  | nA   | Vce=10V<br>Ee=0mW/cm <sup>2</sup>    |
| On State Collector Current           | IC(ON)   | LTR-4206  | 1    | 4    |      | mA   | VcE=5V<br>Ee=1mW/cm <sup>2</sup>     |
|                                      |          | LTR-4206E | 1    | 2    |      |      | $\lambda = 940$ nm                   |

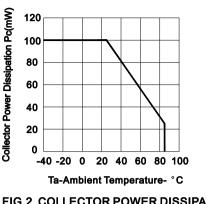
# Typical Electrical/Optical Characteristic Curves (25℃ Ambient Temperature Unless Otherwise Noted)



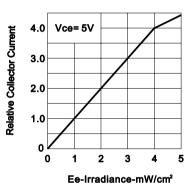














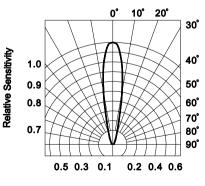


FIG.5 SENSITIVITY DIAGRAM